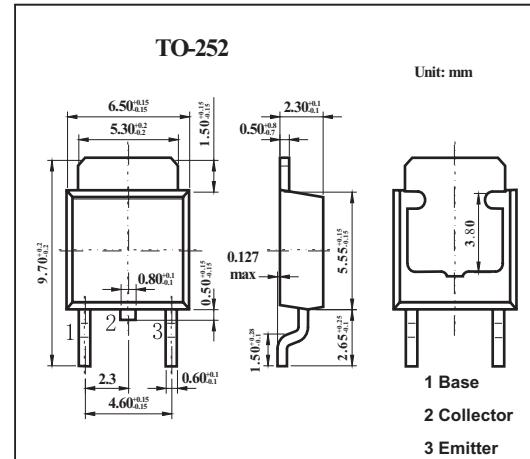


High-Current Switching Applications

2SC4306

■ Features

- Low saturation voltage.
- Fast switching speed.
- Large current capacity.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CBO}	30	V
Collector-emitter voltage	V _{C EO}	20	V
Emitter-base voltage	V _{EBO}	5	V
Collector current	I _C	8	A
Collector current (pulse)	I _{CP}	12	A
Base current	I _B	1.5	A
Collector dissipation T _c =25°C	P _C	1	W
	P _C	15	W
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

2SC4306

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cutoff current	I _{CBO}	V _{CB} = 20V, I _E =0			1	μA
Emitter cutoff current	I _{EBO}	V _{EB} = 4V, I _C =0			1	μA
DC current gain	h _{FE}	V _{CE} = 2V , I _C = 500mA	100		400	
		V _{CE} = 2V , I _C = 6A	70			
Gain bandwidth product	f _T	V _{CE} = 2V , I _C = 500mA		250		MHz
Output capacitance	C _{ob}	V _{CB} = 10V , f = 1.0MHz		60		pF
Collector-emitter saturation voltage	V _{CESat}	I _C = 5A , I _B = 250mA		220	400	mV
Base-emitter saturation voltage	V _{BESat}	I _C = 5A , I _B = 250mA		1	1.3	V
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = 10μA , I _E = 0	30			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = 1mA , R _{BE} = ∞	20			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E = 10μA , I _C = 0	5			V
Turn-on time	t _{on}			30	300	ns
Storage time	t _{stg}			250	1000	ns
Fall time	t _f			15	150	ns

■ hFE Classification

Rank	R	S	T
hFE	100~200	140~280	200~400